

Title (en)

METHOD FOR CONVERTING SEMICONDUCTOR LAYERS

Title (de)

VERFAHREN ZUM KONVERTIEREN VON HALBLEITERSCHICHTEN

Title (fr)

PROCÉDÉ DE CONVERSION DE COUCHES DE SEMI-CONDUCTEURS

Publication

EP 2647264 A1 20131009 (DE)

Application

EP 11788095 A 20111110

Priority

- DE 102010062386 A 20101203
- EP 2011069854 W 20111110

Abstract (en)

[origin: WO2012072401A1] The present invention relates to a method for converting semiconductor layers, in particular for converting amorphous silicon layers into crystalline silicon layers, in which the conversion is effected by treating the semiconductor layer with a plasma which is generated by a plasma source fitted with a plasma nozzle (1). Moreover, the present invention relates to semiconductor layers produced by the method, electronic and optoelectronic products comprising such semiconductor layers and a plasma source for carrying out the method according to the invention.

IPC 8 full level

H05H 1/26 (2006.01); **H01L 21/02** (2006.01)

CPC (source: EP US)

B23K 10/00 (2013.01 - US); **H01L 21/02027** (2013.01 - US); **H01L 21/02521** (2013.01 - EP US); **H01L 21/02532** (2013.01 - EP US); **H01L 21/02689** (2013.01 - EP US); **H01L 21/3003** (2013.01 - EP US); **H01L 29/04** (2013.01 - US); **H01L 31/1872** (2013.01 - EP US); **H05H 1/32** (2013.01 - EP US); **Y02E 10/50** (2013.01 - US); **Y02P 70/50** (2015.11 - EP US)

Citation (search report)

See references of WO 2012072401A1

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)

DE 102010062386 A1 20120606; **DE 102010062386 B4 20141009**; CN 103229602 A 20130731; CN 103229602 B 20180831; EP 2647264 A1 20131009; JP 2014502424 A 20140130; TW 201242050 A 20121016; TW I602316 B 20171011; US 2013240892 A1 20130919; WO 2012072401 A1 20120607

DOCDB simple family (application)

DE 102010062386 A 20101203; CN 201180058196 A 20111110; EP 11788095 A 20111110; EP 2011069854 W 20111110; JP 2013541277 A 20111110; TW 100143936 A 20111130; US 201113885316 A 20111110